

2SK0601G

Silicon N-channel MOSFET

For switching circuits

■ Features

- Low drain-source ON resistance $R_{DS(on)}$
- High-speed switching
- Allowing to be driven directly by CMOS and TTL
- Mini-power type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing.

■ Package

- Code
MiniP3-F2
- Pin Name
1: Gate
2: Drain
3: Source

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	80	V
Gate-source voltage (Drain open)	V_{GSO}	20	V
Drain current	I_D	0.5	A
Peak drain current	I_{DP}	1.0	A
Power dissipation *	P_D	1	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Marking Symbol: O

Note) *: PC board: Copper foil of the drain portion should have a area of 1 cm² or more and the board thickness should be 1.7 mm.

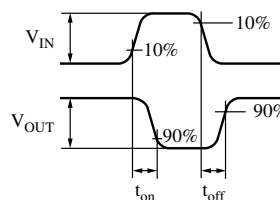
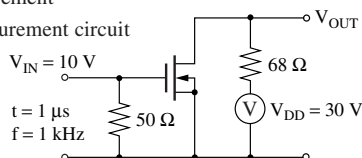
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

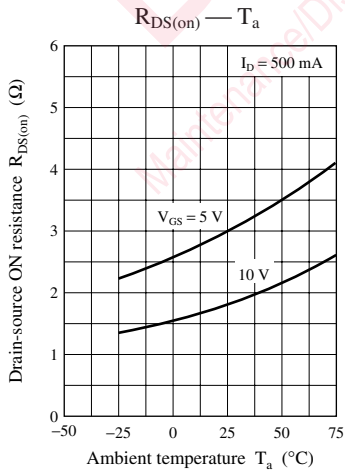
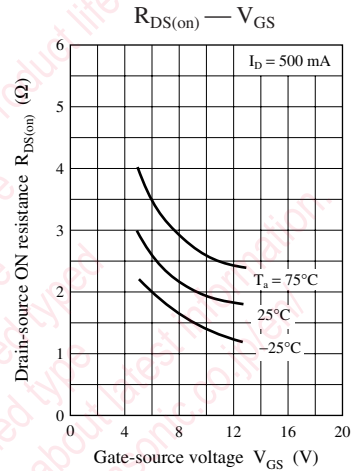
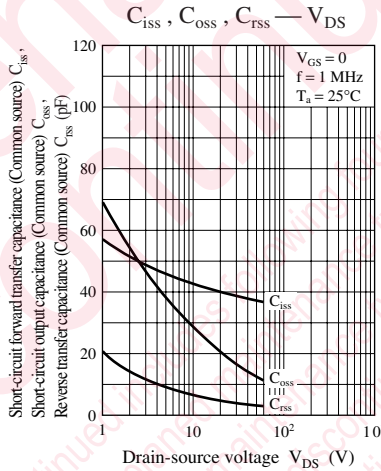
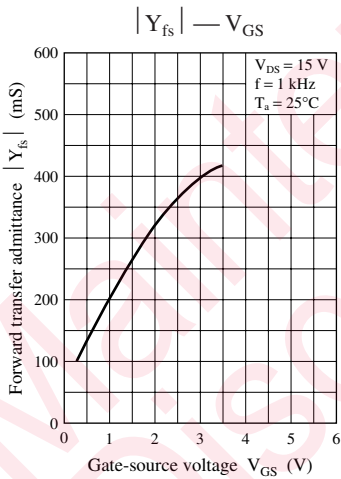
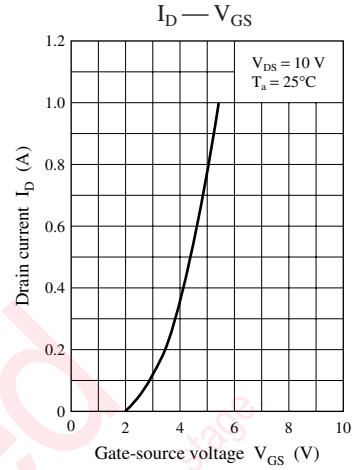
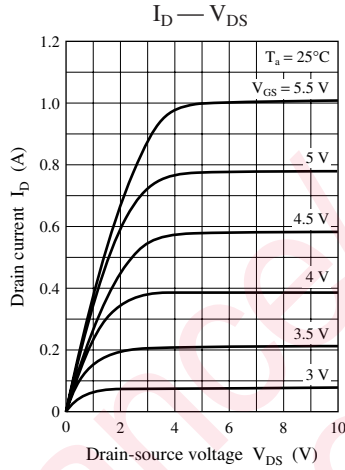
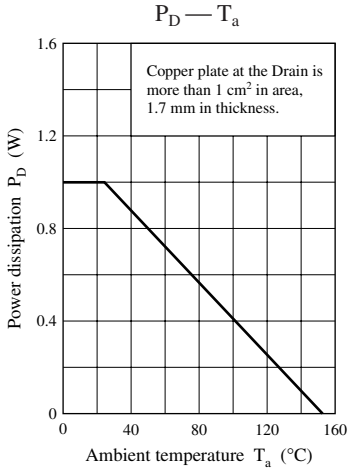
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_{DS} = 100 \mu\text{A}$, $V_{GS} = 0$	80			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0$			10	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = 20 \text{ V}$, $V_{DS} = 0$			0.1	μA
Gate threshold voltage	V_{th}	$I_D = 1 \text{ mA}$, $V_{DS} = V_{GS}$	1.5		3.5	V
Drain-source ON resistance *1	$R_{DS(on)}$	$I_D = 0.5 \text{ A}$, $V_{GS} = 10 \text{ V}$		2	4	Ω
Forward transfer admittance	$ Y_{fs} $	$I_D = 0.2 \text{ A}$, $V_{DS} = 15 \text{ V}$, $f = 1 \text{ kHz}$		300		mS
Short-circuit forward transfer capacitance (Common source)	C_{iss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$		45		pF
Short-circuit output capacitance (Common source)	C_{oss}			30		pF
Reverse transfer capacitance (Common source)	C_{rss}			8		pF
Turn-on time *2	t_{on}			15		ns
Turn-off time *2	t_{off}			20		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

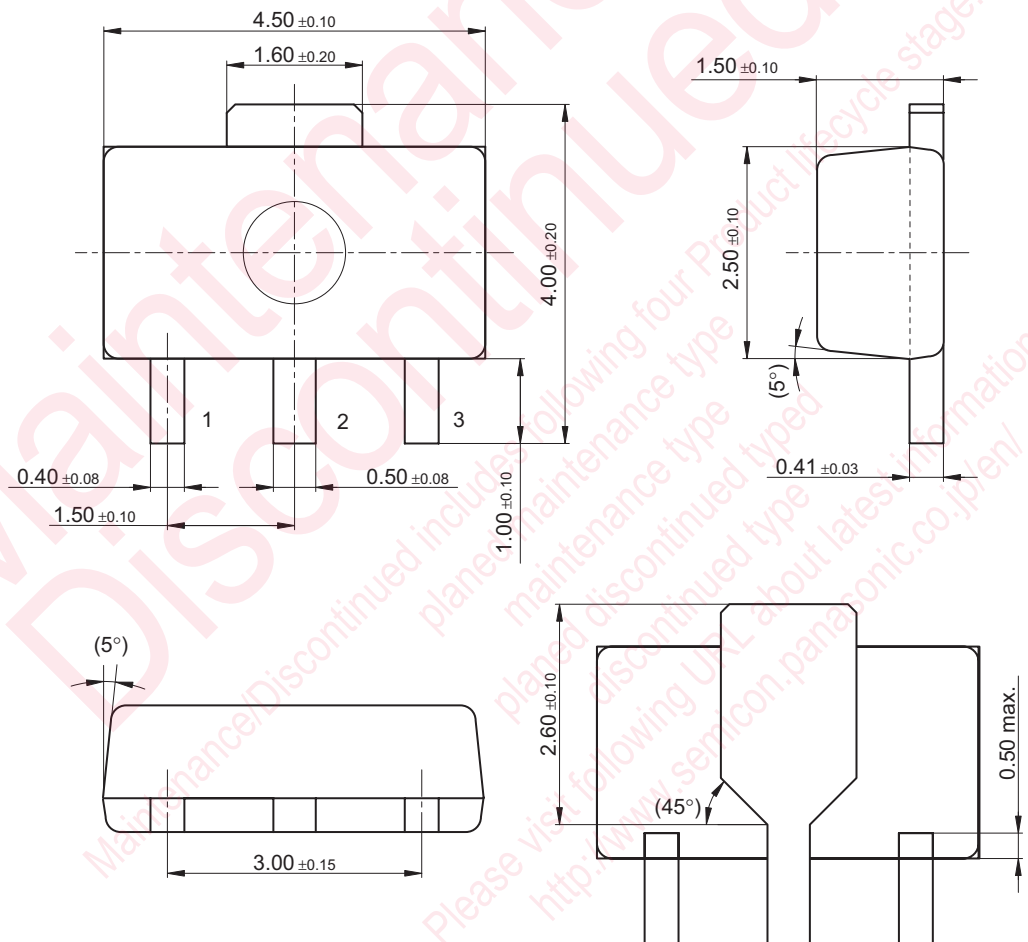
*2: t_{on} , t_{off} measurement circuit





MiniP3-F2

Unit: mm



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